

SILICON TRANSISTOR ARRAY

 μ PA1434

NPN SILICON POWER TRANSISTOR ARRAY LOW SPEED SWITCHING USE INDUSTRIAL USE

DESCRIPTION

The μ PA1434 is NPN silicon epitaxial Power Transistor Array that built in 4 circuits designed for driving solenoid, relay, lamp and so on.

FEATURES

- · Easy mount by 0.1 inch of terminal interval.
- High hre. Low Vce(sat).
 hre = 800 to 3200 (at Ic = 0.5 A)
 Vce(sat) = 0.5 V MAX. (at Ic = 2 A)

ORDERING INFORMATION

Part Numb	er P	ackage	Quality Grade	
μPA1434ŀ	H 10	Pin SIP	Standard	

Please refer to "Quality grade on NEC Semiconductor Device" (Document number IEI-1209) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Collector to Base Voltage	Vсво	60	V		
Collector to Emitter Voltage	VCEO	60	V		
Emitter to Base Voltage	VEBO	7	V		
Collector Current (DC)	Ic(DC)	3	A/unit		
Collector Current (pulse)	C(pulse)*	6	A/unit		
Base Current (DC)	B(DC)	0.6	A/unit		
Total Power Dissipation	P _{T1} **	3.5	W		
$(T_a = 25 ^{\circ}C)$					
Total Power Dissipation	P _{T2} **	28	W		
$(T_c = 25 ^{\circ}C)$					
Junction Temperature	Tj	150	°C		
Storage Temperature	Tstg -55	to +150) °C		
* PW \leq 300 μ s, Duty Cycle \leq 10 %					

PACKAGE DIMENSION
(in millimeters)

26.8 MAX.

26.8 MAX.

1.4 0.6 ± 0.1

25.4

1.4 0.6 ± 0.1

20.5 ± 0.1

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20.6 ± 0.1

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20.8 MAX.

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The information in this document is subject to change without notice.

** 4 Circuits

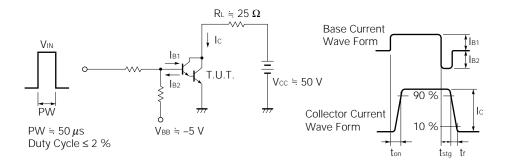


ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Leakage Current	Ісво			10	μΑ	Vcb = 60 V, IE = 0	
Emitter Leakage Current	Ієво			10	μΑ	V _{EB} = 5 V, I _C = 0	
DC Current Gain	h _{FE1} *	800		3200	_	Vce = 5 V, Ic = 0.5 A	
DC Current Gain	h _{FE2} *	500			_	Vce = 5 V, Ic = 3 A	
Collector Saturation Voltage	VcE(sat) *			0.5	V	Ic = 2 A, I _B = 20 mA	
Base Saturation Voltage	V _{BE(sat)} *			1.2	V	Ic = 2 A, I _B = 20 mA	
Turn On Time	ton		1		μs	Ic = 2 A	
Storage Time	tstg		3		μs	$I_{B1} = -I_{B2} = 10 \text{ mA}$ $V_{CC} = 50 \text{ V}, R_L = 25 \Omega$	
Fall Time	tf		1.5		μs	See test circuit	

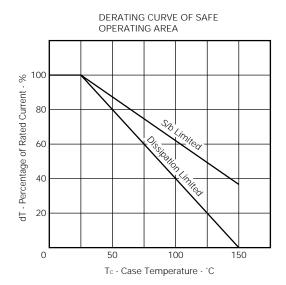
^{*} PW \leq 350 μ s, Duty Cycle \leq 2 % /pulsed

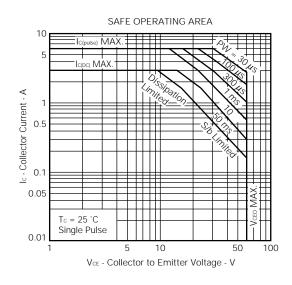
SWITCHING TIME TEST CIRCUIT

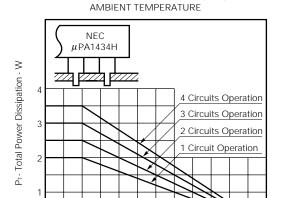




TYPICAL CHARACTERISTICS (Ta = 25 °C)







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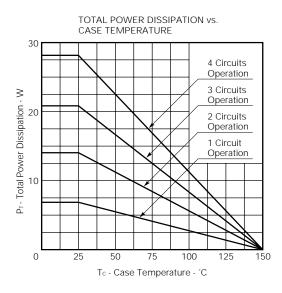
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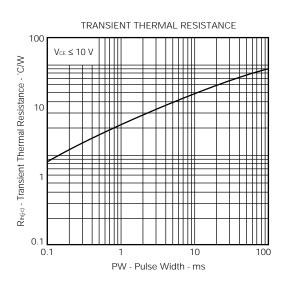
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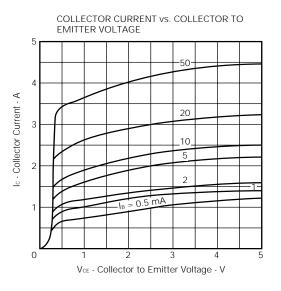
Ta - Ambient Temperature - °C

125

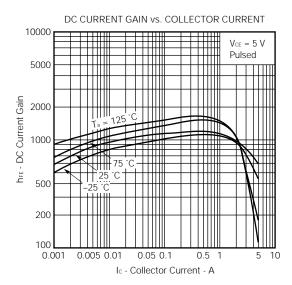
TOTAL POWER DISSIPATION vs.

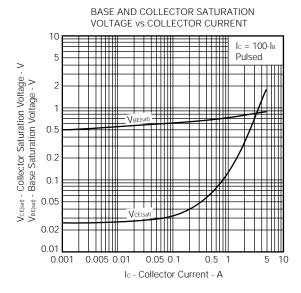














REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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